

## 檢測技術 I

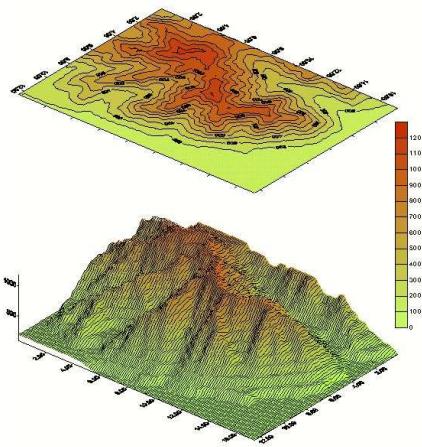
### 掃瞄探針顯微術

#### Scanning probe microscope 分類

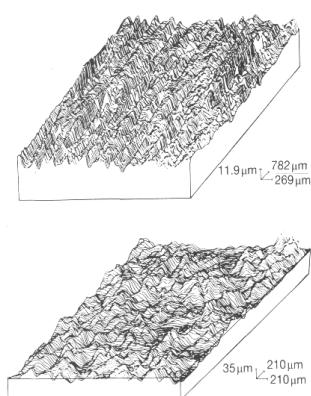
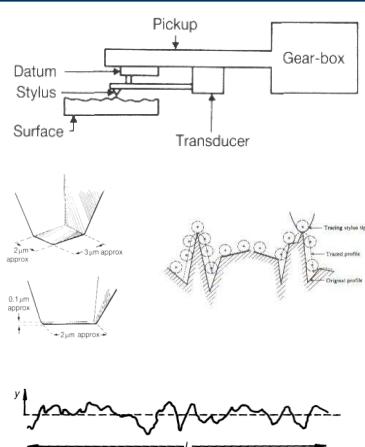
- Scanning tunneling microscope (STM, 掃瞄穿遂顯微鏡)
- Atomic force microscope (AFM, 原子力顯微鏡)
- Near-field scanning optical microscope (NSOM, 近場光學顯微鏡)

## What is SPM good for?

- AFM is a tool for detecting **Surface Topography**.
- Flat, solid surfaces with small (<1μm) features make suitable specimens.
- Length and height measurements are possible and relatively precise (compared to scanning electron microscopy).

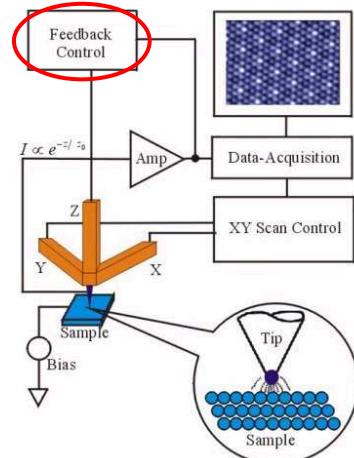
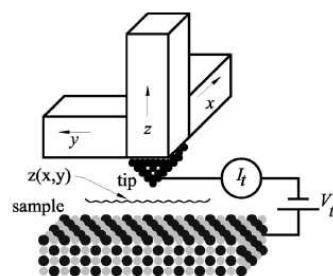


## 前身 surface stylus profiler



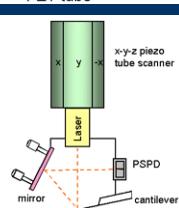
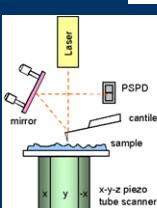
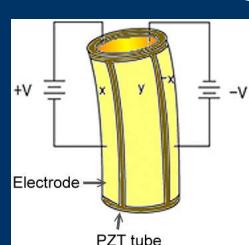
Images from Hutchings, *Tribology* (1992) and Thomas, *Rough Surfaces* (1999).

## 成像原理

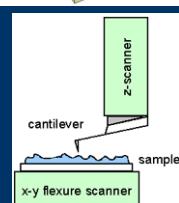
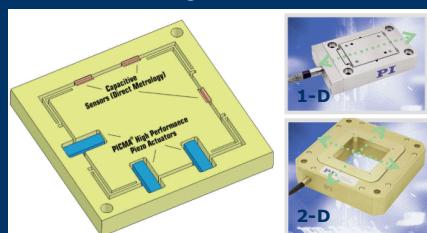


## Fine positioner

### Piezo tube



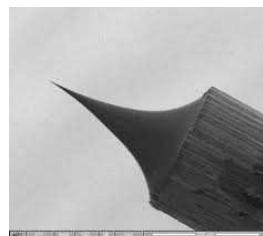
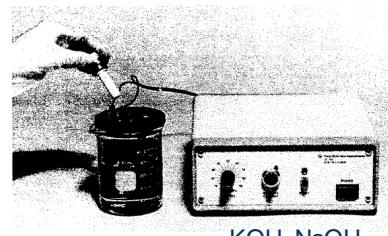
### Flexure Stage



- X-Y plane and Z axis orthogonal
- Faster response
- More robust

## Conductive tip for STM

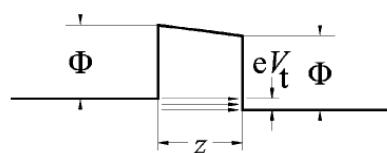
- Tip material: W, PtIr



From mse.engin.umich.edu

## Tunneling effect

$$I_t(z) = I_0 e^{-2\kappa_t z}$$

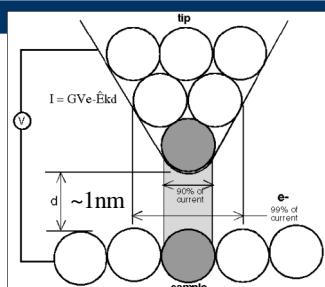


where  $I_0$  is a function of the applied voltage and the density of states in both tip and sample and  $\kappa_t = \sqrt{2m\Phi/\hbar}$

For metals,  $\Phi = 4\text{eV}$ , thus  $\kappa_t \sim 1\text{\AA}^{-1}$ . When  $z$  is increased by one angstrom, the current drops by an order of magnitude.

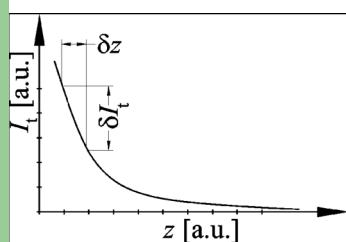
STMs cannot image insulating materials.

## Tunneling effect



I is an exponential function of z.

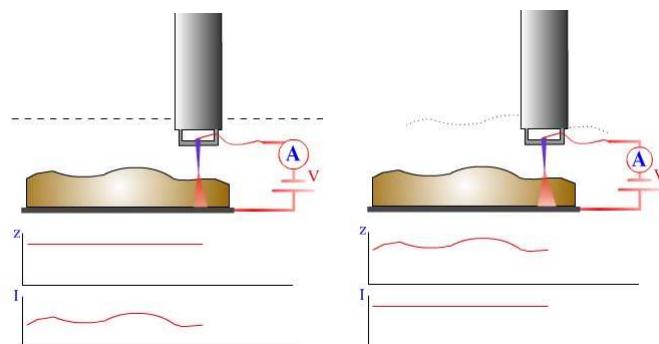
Sensitivity along z



sub-angstrom precision vertically  
(atomic resolution laterally)

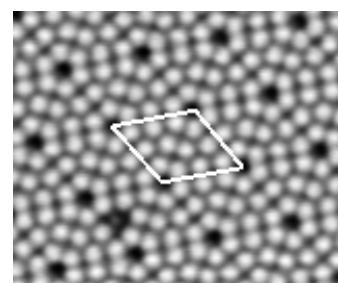
## Imaging principle

- Constant height mode
- Constant current mode



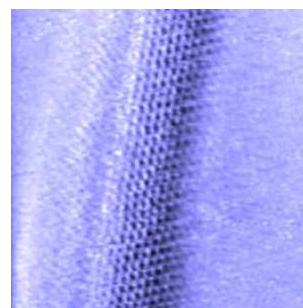
From NT-MDT

## Si(111) 7x7 surface



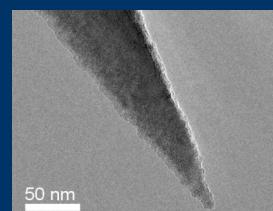
## Carbon nanotube

- STM image of carbon nanotube deposited on HOPG substrate. Atomic structure of nanotube is clearly visible.

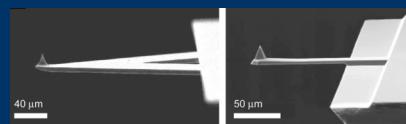


From NT-MDT

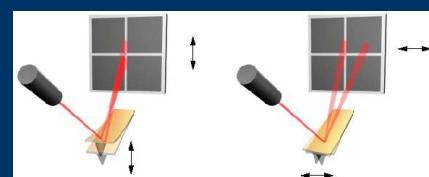
## Tip and Cantilever for AFM



- Sharp tip → Small contact area
- mN/ $\mu$ N loads would destroy the tip, or indent the specimen
- Mechanism for pN~nN loads needed!

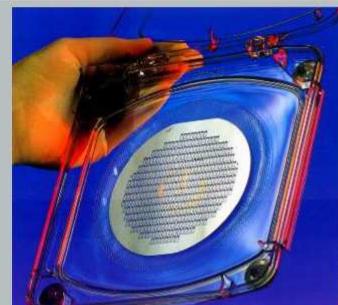


- Microfabricated Si/Si<sub>3</sub>N<sub>4</sub> structures
- Bending can be detected by laser reflection.

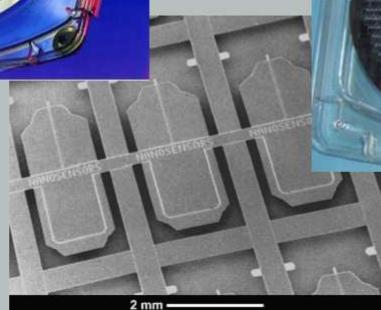


### General remarks - Batch Fabrication

**NANO WORLD**  
INNOVATIVE TECHNOLOGIES



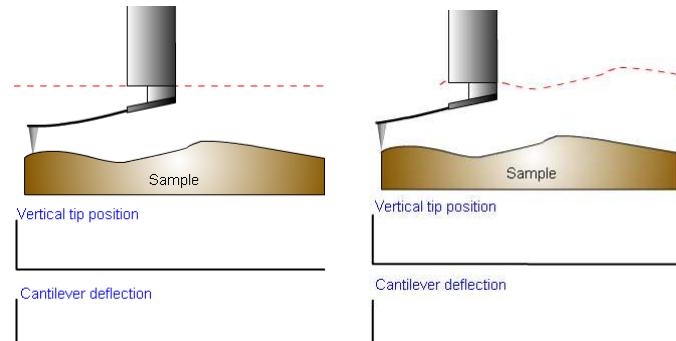
4-inch wafer  
with 388 probes



6-inch wafer with more  
than 1000 probes

## Imaging principle

- Constant height mode (Z servo off) → error signal
- Constant force mode (Z servo on) → topography

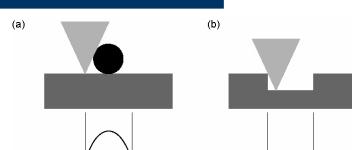


From NT-MDT

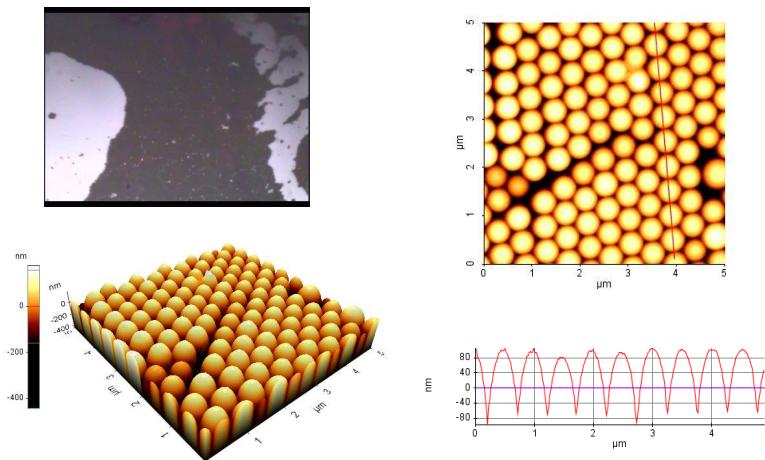
## Contact AFM – constant force imaging

- Cantilever bending is kept constant.
- Z positioner voltage is recorded.

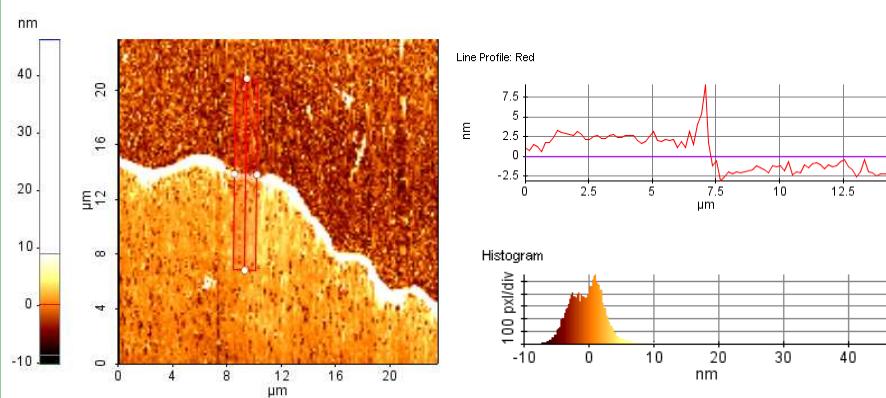
Z voltage



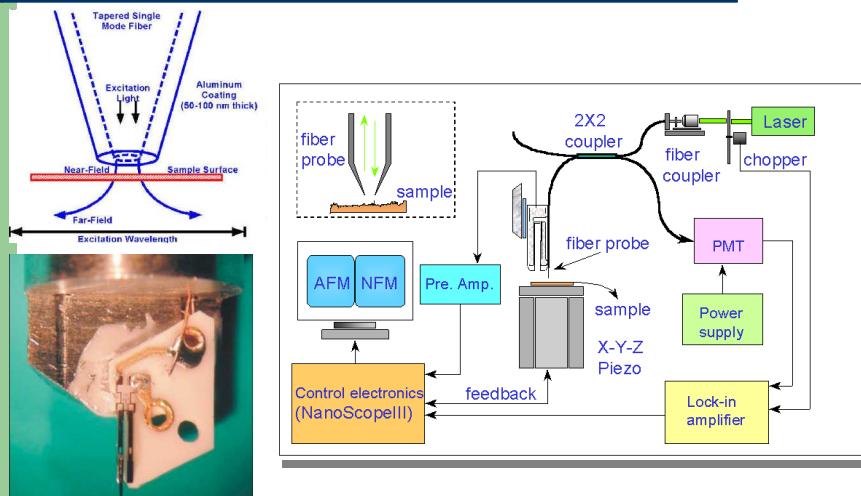
## 500nm nanospheres



## Step height



## NSOM



## Hollow tips for NSOM

- Fiber tip
- Nanofabricated AFM tip

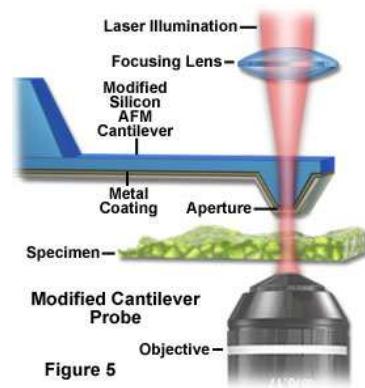
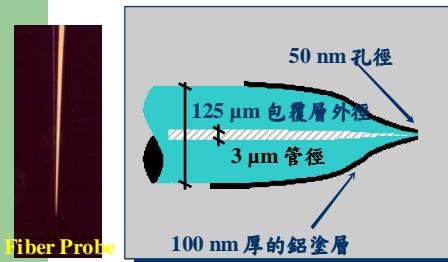
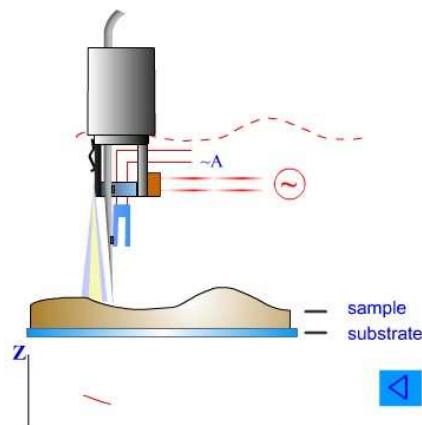


Figure 5

From Olympus

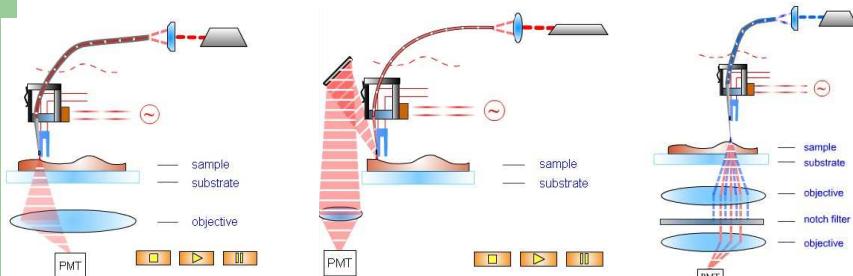
## Shear force



From NT-MDT

## Transmission mode

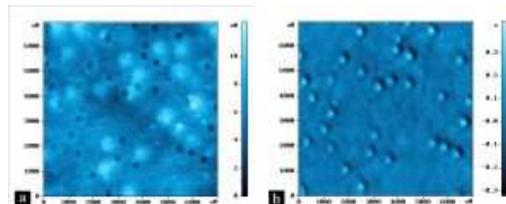
- Transmission mode
- Reflection mode
- Luminescence mode



From NT-MDT

## Quantum dots

- Shear Force (topography) (a) and reflection (b) images of In-Ga quantum dots made with the use of He-Cd 442 nm laser.



From NT-MDT

## 延伸課程

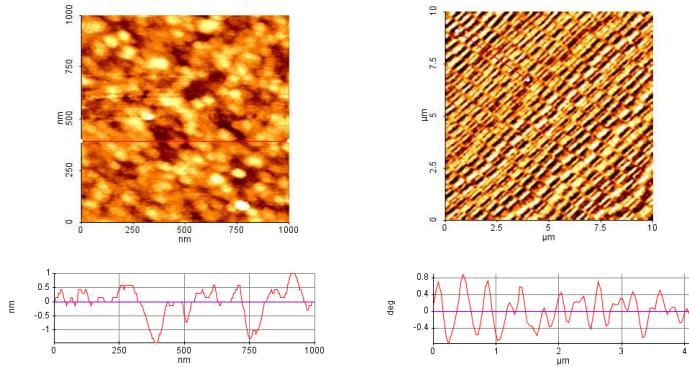
- 掃瞄探針顯微術(下學期, 大四碩一合授)
- 多功能掃瞄探針顯微鏡 (Park Systems XE-100)  
contact AFM  
non-contact AFM  
lift-mode operation  
phase detection  
lateral force microscopy  
force modulation microscopy  
dynamic magnetic force microscopy  
electrostatic force microscopy  
dynamic-contact EFM  
piezoresponse force microscopy  
scanning Kelvin probe microscopy  
high-voltage nanolithography



From Park Systems

## Magnetic domains

- IBM deskstar 20GB HD



## Ferroelectric domains

- BiFeO<sub>3</sub>

